Spread Spectrum Clock Generator

MB88155

■ DESCRIPTION

MB88155 is a clock generator for EMI (Electro Magnetic Interference) reduction. The peak of unnecessary radiation noise (EMI) can be attenuated by making the oscillation frequency slightly modulate periodically with the internal modulator. For modulation, the MB88155 supports both center-spreading and down-spreading. It has a non-modulated clock output pin (REFOUT) as well as a modulated clock output pin (CKOUT).

■ FEATURES

• Input frequency: 12.5 MHz to 50 MHz (Multiplied by 1)

12.5 MHz to 20 MHz (Multiplied by 4)

• Output frequency: CKOUT 12.5 MHz to 80 MHz

REFOUT The same as input frequency (not multiplied)

- Modulation rate : $\pm 0.5\%$, $\pm 1.0\%$ (center spread) , -1.0%, -2.0% (Down spread)
- Equipped with oscillation circuit: range of oscillation 12.5 MHz to 40 MHz (Fundamental oscillation)

40 MHz to 48 MHz (3rd overtone)

- Modulation clock output Duty: 40% to 60%
- Modulation clock cycle cycle jitter: MB88155-1xx 12.5 MHz to 20 MHz less than 150 ps

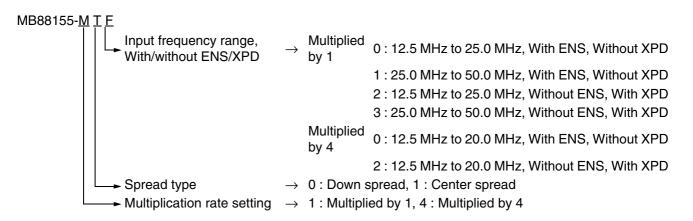
MB88155-1xx 20 MHz to 50 MHz less than 100 ps MB88155-4xx less than 200 ps

- Low current consumption by CMOS process : 5 mA (24 MHz : Typ-sample, no load)
- Power supply voltage : 3.3 V \pm 0.3 V
- Operating temperature : 40 °C to +85 °C
- Package: 8-pin plastic TSSOP



■ PRODUCT LINEUP

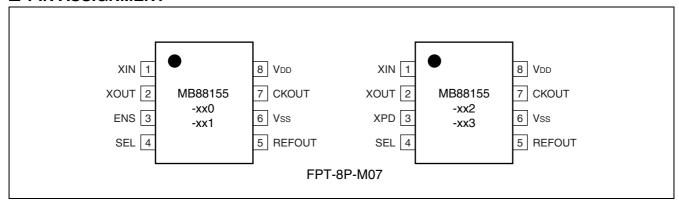
The MB88155 is available in different models : 2 models different in multiplier (\times 1 and \times 4) , 2 in modulation type (center-spreading and down-spreading) , 2 in input frequency range at a multiplier of 1 (12.5 MHz to 25 MHz and 25 MHz to 50 MHz) , and 1 in input frequency range at a multiplier of 4 (12.5 MHz to 20 MHz) . The MB88155 is also available in two versions : modulation-on/off selectable version (with ENS pin) and power-down function built-in version (with XPD pin) .



Line-up of MB88155

Product	Input frequency	Multiplication rate	Output frequency	Modulation type	Modulation enable pin	Power down pin
MB88155-100	12.5 MHz to 25 MHz		The same as input frequency		Vaa	No
MB88155-101	25 MHz to 50 MHz			Down	Yes	INO
MB88155-102	12.5 MHz to 25 MHz			spread	No	Vac
MB88155-103	25 MHz to 50 MHz	Multiplied by 1				Yes
MB88155-110	12.5 MHz to 25 MHz	Multiplied by 1		Center spread	Yes	No
MB88155-111	25 MHz to 50 MHz				165	INO
MB88155-112	12.5 MHz to 25 MHz				No	Yes
MB88155-113	25 MHz to 50 MHz				INO	162
MB88155-400				Down	Yes	No
MB88155-402	10 E MUZ to 20 MUZ	Multiplied by 4	50 MHz to	spread	No	Yes
MB88155-410	12.5 MHz to 20 MHz	iviuitipiied by 4	80 MHz	Center	Yes	No
MB88155-412				spread	No	Yes

■ PIN ASSIGNMENT



■ PIN DESCRIPTION

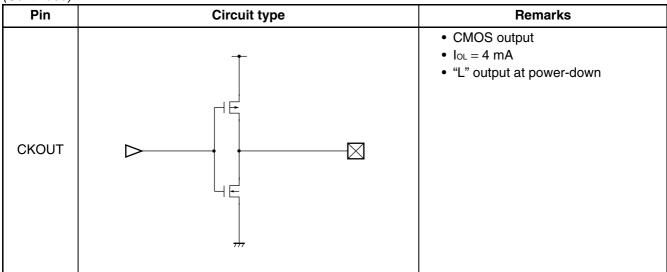
Pin name	I/O	Pin no.	Description
XIN	I	1	Connection pin of resonator/clock input pin
XOUT	0	2	Connection pin of resonator
ENS/XPD	I	3	Modulation enable pin/power down pin
SEL	I	4	Modulation rate setting pin Down spread, SEL = "L" : Modulation rate -1.0% Down spread, SEL = "H" : Modulation rate -2.0% Down spread, SEL = "L" : Modulation rate $\pm 0.5\%$ Down spread, SEL = "H" : Modulation rate $\pm 1.0\%$
REFOUT	0	5	Non-modulated clock output pin This pin becomes to "L" at power-down.
Vss	_	6	GND Pin
CKOUT	0	7	Modulated clock output pin This pin becomes to "L" at power-down.
V _{DD}	_	8	Power supply voltage pin

■ I/O CIRCUIT TYPE

Pin	Circuit type	Remarks
SEL, XPD		CMOS hysteresis input
ENS	50 kΩ Solve Solv	CMOS hysteresis input with pull-up resistor of 50 kΩ (Typ)
REFOUT		 CMOS output IoL = 3 mA "L" output at power-down

(Continued)

(Continued)



Note: For XIN pin and XOUT pin, refer to "■ OSCILLATION CIRCUIT".

■ HANDLING DEVICES

Preventing Latch-up

A latch-up can occur if, on this device, (a) a voltage higher than V_{DD} or a voltage lower than V_{SS} is applied to an input or output pin or (b) a voltage higher than the rating is applied between V_{DD} and V_{SS} . The latch-up, if it occurs, significantly increases the power supply current and may cause thermal destruction of an element. When you use this device, be very careful not to exceed the maximum rating.

Handling unused pins

Do not leave an unused input pin open, since it may cause a malfunction. Handle by, using a pull-up or pull-down resistor.

Unused output pin should be opened.

The attention when the external clock is used

Input the clock to XIN pin, and XOUT pin should be opened when you use the external clock. Please pay attention so that an overshoot and an undershoot do not occur to an input clock of XIN pin.

Power supply pins

Please design connecting the power supply pin of this device by as low impedance as possible from the current supply source.

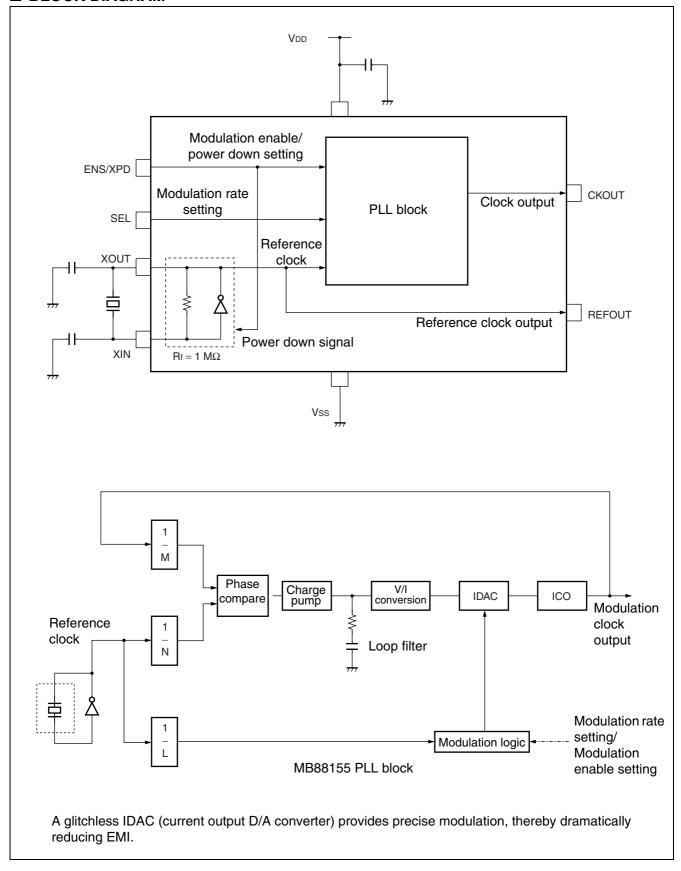
We recommend connecting electrolytic capacitor (about 10 μ F) and the ceramic capacitor (about 0.01 μ F) in parallel between Vss and V_{DD} near the device, as a bypass capacitor.

Oscillation circuit

Noise near the XIN and XOUT pins may cause the device to malfunction. Design printed circuit boards so that electric wiring of XIN or XOUT pin and the resonator do not intersect other wiring.

Design the printed circuit board that surrounds the XIN and XOUT pins with ground.

■ BLOCK DIAGRAM



■ PIN SETTING

The modulation clock requires stabilization wait time after the PIN setting is changed. For the modulation clock stabilization wait time, assure the maximum value for "Lock-up time" in the AC Characteristics list in "

ELECTRICAL CHARACTERISTICS".

ENS modulation enable setting

ENS	Modulation					
L	No modulation	MB88155-xx0, xx1				
Н	Modulation	WID00133-XXU, XX1				

Note: Spectrum does not diffuse when "L" is set to ENS pin. MB88155-xx2, xx3 do not have ENS pin.

XPD power down

XPD		Status					
L	Power down status	MB88155-xx2, xx3					
Н	Operating status	WID00133-XX2, XX3					

Note: When setting "L" to XPD pin, it becomes power down mode (low power consumption mode). Both CKOUT and REFOUT of output pins are fixed to "L" output during power down. MB88155-xx0, xx1 do not have XPD pin.

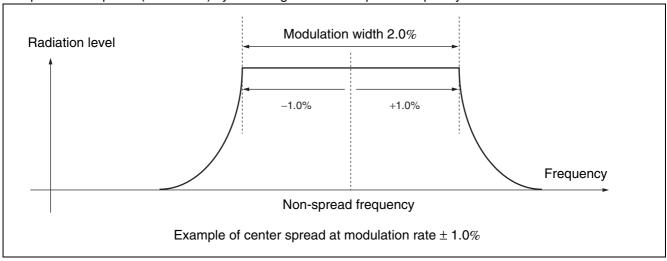
SEL modulation rate setting

SEL	Frequ	uency
l	± 0.5%	MB88155-x1x
_	- 1.0%	MB88155-x0x
П	± 1.0%	MB88155-x1x
	- 2.0%	MB88155-x0x

Note: The modulation rate can be changed at the level of the pin.

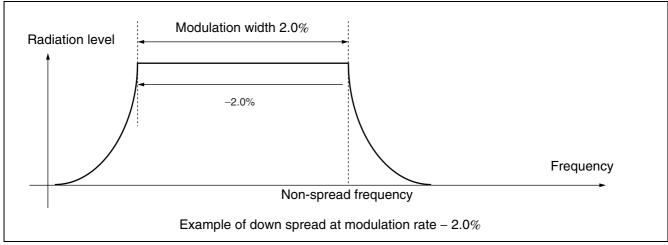
• Center spread

Spectrum is spread (modulated) by centering on the non-spread frequency.



• Down spread

Spectrum is spread (modulated) below the non-spread frequency.

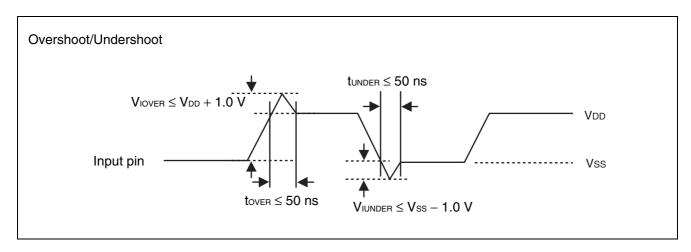


■ ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Rat	ing	Unit
Faranielei	Symbol	Min	Max	Offic
Power supply voltage*	V _{DD}	- 0.5	+ 4.0	V
Input voltage*	Vı	Vss - 0.5	V _{DD} + 0.5	V
Output voltage*	Vo	Vss - 0.5	V _{DD} + 0.5	V
Storage temperature	Tst	– 55	+ 125	°C
Operation junction temperature	Tu	- 40	+ 125	°C
Output current	lo	- 14	+ 14	mA
Overshoot	VIOVER	_	$V_{\text{DD}} + 1.0 \text{ (tover} \le 50 \text{ ns)}$	V
Undershoot	Viunder	Vss - 1.0 (tunder ≤ 50 ns)	_	V

 $^{^{\}star}$: The parameter is based on Vss = 0.0 V.

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.



■ RECOMMENDED OPERATING CONDITIONS

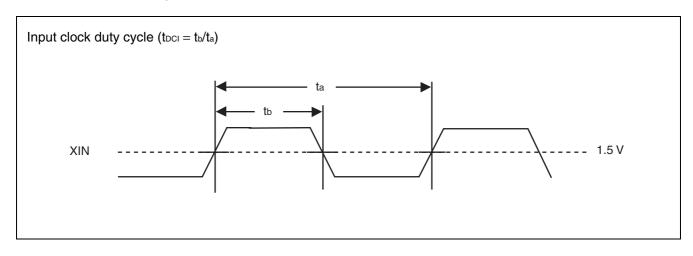
(Vss = 0.0 V)

Parameter	Symbol	Pin	Conditions		Unit		
Parameter	Symbol	PIII	Conditions	Min	Тур	Max	Offic
Power supply voltage	V _{DD}	V_{DD}	_	3.0	3.3	3.6	V
"H" level input voltage	Vıн	XIN, SEL, ENS, XPD	_	$V_{\text{DD}} \times 0.8$	_	V _{DD} + 0.3	V
"L" level input voltage	VıL	XIN, SEL, ENS, XPD	_	Vss		$V_{\text{DD}} \times 0.2$	٧
Input clock duty cycle	tocı	XIN	12.5 MHz to 50 MHz	40	50	60	%
Operating temperature	Ta	_	_	- 40	_	+ 85	°C

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their FUJITSU representatives beforehand.



■ ELECTRICAL CHARACTERISTICS

• DC Characteristics

(Ta = -40 °C to +85 °C, V_{DD} = 3.3 V \pm 0.3 V, V_{SS} = 0.0 V)

Downwater	Cumbal	D:	Conditions		Value		l lm!s	
Parameter	Symbol	PIN	Pin Conditions		Тур	Max	Unit	
Power supply current	Icc	V _{DD}	24 MHz output No load capacitance	_	5.0	7.0	mA	
			At power-down	_	10	_	μΑ	
	Vонс	CKOUT	"H" level output Іон = -4 mA	V _{DD} – 0.5		V _{DD}	V	
Output voltage	Vohr	REFOUT	"H" level output Іон = - 3 mA	- VDD - 0.5	_	V DD	V	
	Volc	CKOUT	"L" level output IoL = 4 mA	Vss		0.4	V	
	Volr	REFOUT	"L" level output IoL = 3 mA	VSS	_	0.4	V	
Output impedance	Zoc	CKOUT	12.5 MHz to 80 MHz	_	45	_	Ω	
Output impedance	Zor	REFOUT	12.5 MHz to 50 MHz	_	70	_	52	
Input capacitance	Cin	XIN, SEL, ENS/XPD	$Ta = +25 ^{\circ}C$ $V_{DD} = V_{I} = 0.0 V$ f = 1 MHz	_	_	16	pF	
Input pull-up resistor	Rpu	ENS	VIL = 0.0 V	25	50	200	kΩ	
		REFOUT	12.5 MHz to 50 MHz	_	_	15		
Load capacitance	CL	OKOLIT	12.5 MHz to 50 MHz	_	_	15	pF	
		CKOUT	50 MHz to 80 MHz	_	_	7		

AC Characteristics

 $(Ta = -40 \, ^{\circ}C \text{ to } + 85 \, ^{\circ}C, \, V_{DD} = 3.3 \, \text{V} \pm 0.3 \, \text{V}, \, \text{Vss} = 0.0 \, \text{V})$

Devementes	Cumbal	Din	·	, 1 00 0, v	Value		Unit
Parameter	Symbol	Pin	Conditions	Min	Тур	Max	Unit
Oscillation	ı	XIN,	Fundamental oscillation	12.5	_	40	N/I I-
frequency	fx	XOUT	3 rd overtone	40 — 48		48	– MHz
			MB88155 – 1x0, 1x2	12.5	_	25	
Input frequency	fin	XIN	MB88155 – 1x1, 1x3	25	_	50	MHz
			MB88155 – 4xx	12.5	_	20	
			MB88155 – 1x0, 1x2	12.5	_	25	
		REFOUT	MB88155 – 1x1, 1x3	25	_	50	
Output fraguesianos			MB88155 – 4xx	12.5		20	N 41 1-
Output frequency	fоит		MB88155 – 1x0, 1x2	12.5	_	25	MHz
		CKOUT	MB88155 – 1x1, 1x3	25		50	
			MB88155 – 4xx	50	_	80	
Outside also make	SRc	СКОИТ	Load capacitance 15 pF, 0.4 V to 2.4 V	0.4	_	4.0	\//
Output slew rate	SRR	REFOUT	Load capacitance 15 pF, 0.4 V to 2.4 V	0.3	_	2.0	V/ns
Output clock	tocc	CKOUT	1.5 V reference level	40		60	67
duty cycle	tocr	REFOUT	1.5 V reference level	t _{DCI} - 10*1		t _{DCI} + 10*1	- %
Modulation frequency	f _{MOD}	СКОИТ	Input frequency at 24 MHz	_	32.4	_	kHz
Lock-up time*2	t LK	CKOUT	_	_	2	5	ms
			MB88155 – 1xx Input frequency 12.5 MHz to 20 MHz, No load capacitance, Ta = $+25$ °C, V _{DD} = 3.3 V, Standard deviation σ	_	_	150	ps
Cycle-cycle jitter	e jitter tuc CKOUT	CKOUT	MB88155 $-$ 1xx Input frequency 20 MHz to 50 MHz, No load capacitance, Ta = $+$ 25 °C, V _{DD} = 3.3 V, Standard deviation σ	_	_	100	ps
			MB88155 $-$ 4xx No load capacitance, Ta = $+$ 25 °C, V _{DD} = 3.3 V, Standard deviation σ	_	_	200	ps

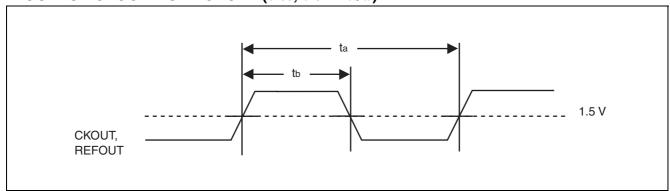
^{*1 :} Duty of the REFOUT output is guaranteed only for the following A and B because it depends on tool of input clock duty.

A. Resonator input: When resonator is connected with XIN pin and XOUT pin, and oscillates normally.

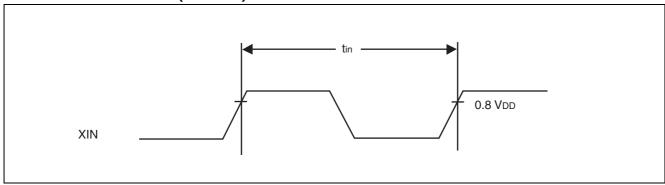
B. External clock input : The input level is Full-swing ($V_{SS} - V_{DD}$).

^{*2 :} The modulation clock requires stabilization wait time after the IC is turned on or released from power-down mode, or after SEL (modulation factor) or ENS (modulation enable) setting is changed. For the modulation clock stabilization wait time, assure the maximum value for the lock-up time.

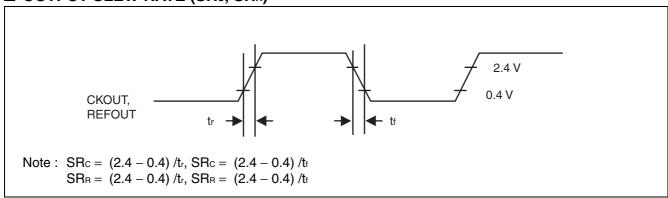
\blacksquare OUTPUT CLOCK DUTY CYCLE (tdcc, tdcR = tb/ta)



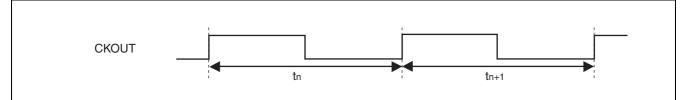
■ INPUT FREQUENCY (fin = 1/tin)



■ OUTPUT SLEW RATE (SRc, SRR)



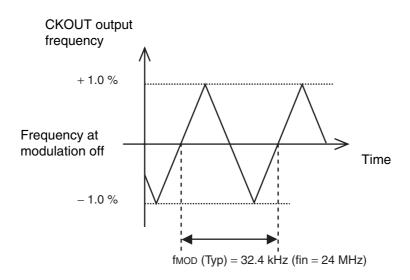
\blacksquare CYCLE-CYCLE JITTER (tJc = |t_n - t_n + {}_1|)



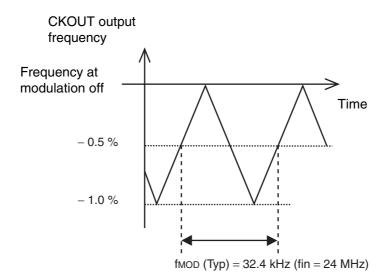
Note: Cycle-cycle jitter indicates the difference between a certain cycle and the immediately succeeding (or preceding) cycle.

■ MODULATION WAVEFORM

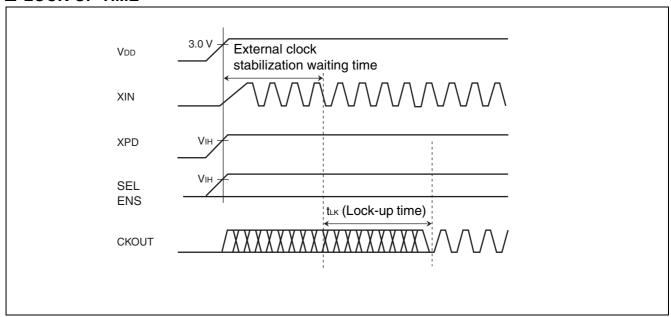
• Modulation rate $\pm 1.0\%$, example of center spread



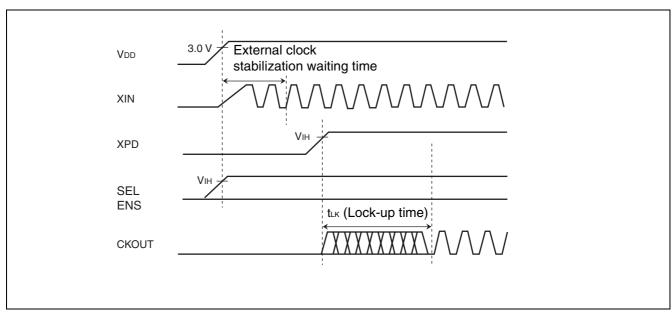
• Modulation rate - 1.0%, example of down spread



■ LOCK-UP TIME

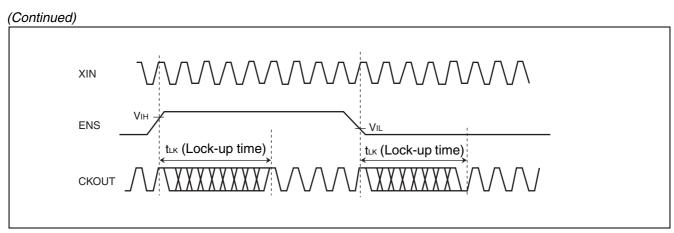


If the XPD pin is fixed at the "H" level, the maximum time after the power is turned on until the set clock signal is output from CKOUT pin is (the stabilization wait time of input clock to XIN pin) + (the lock-up time "tlk"). For the input clock stabilization time, check the characteristics of the resonator or oscillator used.



If the XPD pin is used for power-down control, the set clock signal is output from the CKOUT pin at most the lock-up time "t_k" after the XPD pin goes "H" level.

(Continued)



If the ENS pin is used for modulation enable control during normal operation, the set clock signal is output from the CKOUT pin at most the lock-up time "tlk" after the level at the ENS pin is determined.

Note: The wait time for the clock signal output from the CKOUT pin to become stable is required after the IC is released from power-down mode by the XPD pin or after another pin's setting is changed. During the period until the output clock signal becomes stable, neither of the output frequency, output clock duty cycle, modulation period, and cycle-cycle jitter characteristic cannot be guaranteed. It is therefore advisable to take action, such as cancelling a device reset at the stage after the lock-up time has passed.

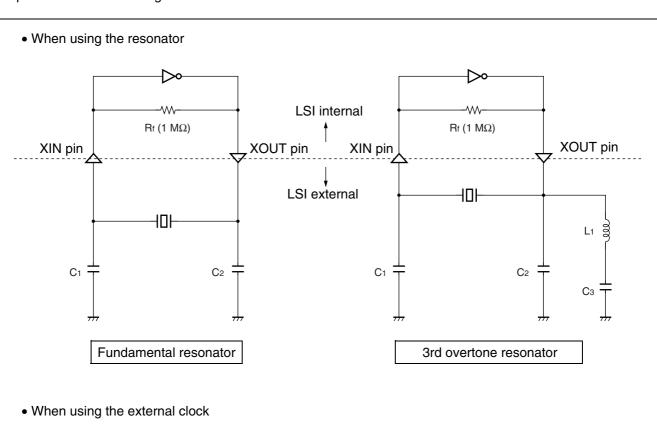
■ OSCILLATION CIRCUIT

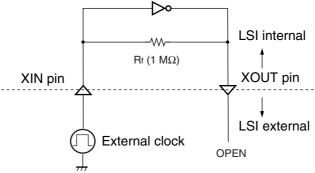
The following schematic on the left-hand side shows a sample connection of a general resonator. The oscillation circuit contains a feedback resistor (1 $M\Omega$). The values of capacitors (C_1 and C_2) must be adjusted to the optimum constant of the resonator used.

The following schematic on the right-hand side shows a sample connection of a 3rd overtone resonator. The values of capacitors (C_1 , C_2 , and C_3) and inductor (L_1) must be adjusted to the optimum constant of the resonator used.

The most suitable value is different by individual resonator. Please refer to the resonator manufacturer which you use for the most suitable value.

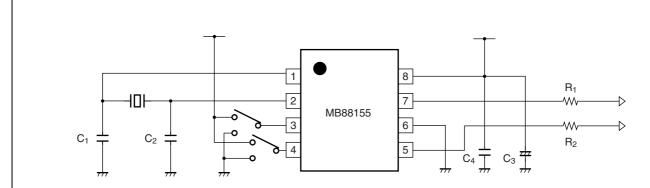
To use an external clock signal (without using the resonator), input the clock signal to the XIN pin with the XOUT pin connected to nothing.





Note: Note that the jitter characteristic of the input clock signal may affect the cycle-cycle jitter characteristic.

■ INTERCONNECTION CIRCUIT EXAMPLE



C₁, C₂ : Oscillation stabilization capacitance (refer to "
OSCILLATION CIRCUIT")

Сз : Capacitor of 10 µF or higher

: Capacitor of about 0.01 μF (connect a capacitor of good high frequency property (ex. laminated ceramic capacitor) to close to this device) C_4

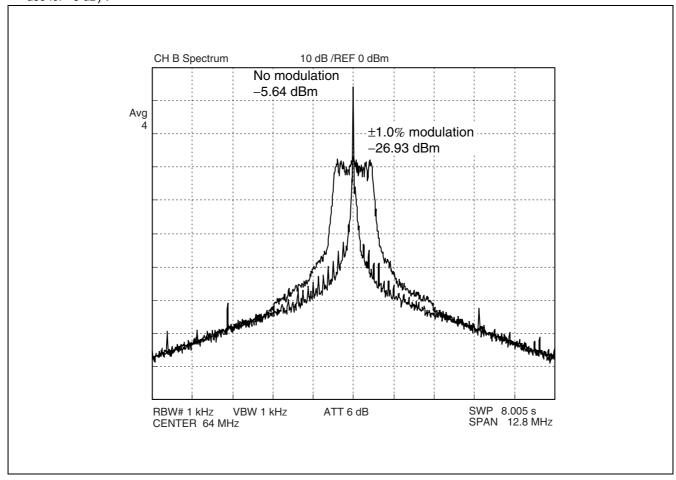
R₁, R₂ : Impedance matching resistor for board pattern

■ SPECTRUM EXAMPLE CHARACTERISTICS

The condition of the examples of the characteristic is shown as follows: Input frequency = 16 MHz (Output frequency = 64 MHz: Using MB88155-410 (Multiplied by 4))

Power-supply voltage = 3.3 V, None load capacity. Modulation rate = \pm 1.0% (center spread).

Spectrum analyzer HP4396B is connected with CKOUT. The result of the measurement with RBW = 1 kHz (ATT use for -6 dB).

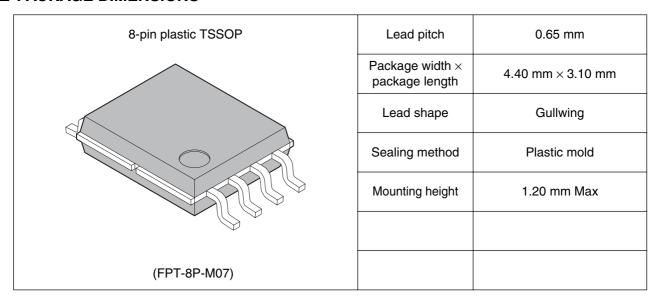


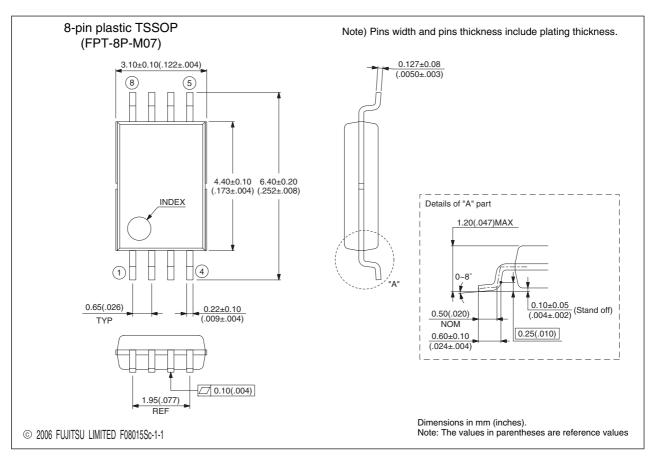
■ ORDERING INFORMATION

Part number	Input frequency	Multiplica- tion rate	Output frequency	Modulation type	Modulation enable pin	Power down pin	Package	Remarks									
MB88155PFT- G-100-JNE1 MB88155PFT- G-101-JNE1	12.5 MHz to 25 MHz 25 MHz to 50 MHz			Down	Yes	No											
MB88155PFT- G-102-JNE1	12.5 MHz to 25 MHz			spread	No	Yes											
MB88155PFT- G-103-JNE1	25 MHz to 50 MHz	Multiplied	The same as input														
MB88155PFT- G-110-JNE1	12.5 MHz to 25 MHz	by 1	frequency		Yes	No											
MB88155PFT- G-111-JNE1	25 MHz to 50 MHz												Center	100	110	8-pin plastic TSSOP	
MB88155PFT- G-112-JNE1	12.5 MHz to 25 MHz											spread	No	Yes	(FPT-8P-M07)		
MB88155PFT- G-113-JNE1	25 MHz to 50 MHz				140	100											
MB88155PFT- G-400-JNE1				Down	Yes	No											
MB88155PFT- G-402-JNE1	12.5 MHz to	Multiplied					spread	No	Yes								
MB88155PFT- G-410-JNE1	20 MHz	by 4					80 MHz	80 MHz	80 MHz	Center	Yes	No					
MB88155PFT- G-412-JNE1				spread	No	Yes											
MB88155PFT- G-100-JN-EFE1	12.5 MHz to 25 MHz				Vaa	Na											
MB88155PFT- G-101-JN-EFE1	25 MHz to 50 MHz	Multiplied	The same as input frequency	as input	as input	Down	Yes	No	8-pin plastic	Emboss							
MB88155PFT- G-102-JN-EFE1	12.5 MHz to 25 MHz	by 1						spread	NI-	V	TSSOP (FPT-8P-M07)	taping (EF type)					
MB88155PFT- G-103-JN-EFE1	25 MHz to 50 MHz				No	Yes											

Part number	Input frequency	Multiplica- tion rate	Output frequency	Modulation type	Modulation enable pin	Power down pin	Package	Remarks									
MB88155PFT- G-110-JN-EFE1					Yes	No											
MB88155PFT- G-111-JN-EFE1	25 MHz to 50 MHz	Multiplied	The same				Center	. 55		8-pin plastic TSSOP	Emboss						
MB88155PFT- G-112-JN-EFE1	12.5 MHz to 25 MHz	by 1	as input frequency	spread	No	Yes	(FPT-8P-M07)	taping (EF type)									
MB88155PFT- G-113-JN-EFE1	25 MHz to 50 MHz				140	103											
MB88155PFT- G-400-JN-EFE1				Down	Yes	No											
MB88155PFT- G-402-JN-EFE1	12.5 MHz to	Multiplied by 4	50 MHz to	spread	No	Yes	8-pin plastic TSSOP	Emboss									
MB88155PFT- G-410-JN-EFE1	20 MHz		80 MHz	Center	Yes	No	(FPT-8P-M07)	taping (EF type)									
MB88155PFT- G-412-JN-EFE1				spread	No	Yes											
MB88155PFT- G-100-JN-ERE1	12.5 MHz to 25 MHz		The same as input frequency		Yes No	No											
MB88155PFT- G-101-JN-ERE1	25 MHz to 50 MHz												Down	165	INO		
MB88155PFT- G-102-JN-ERE1	12.5 MHz to 25 MHz											spread	No	Vaa			
MB88155PFT- G-103-JN-ERE1	25 MHz to 50 MHz	Multiplied					No	Yes									
MB88155PFT- G-110-JN-ERE1		by 1			Yes	No	lo 8-pin plastic TSSOP										
MB88155PFT- G-111-JN-ERE1				Center				Emboss taping									
MB88155PFT- G-112-JN-ERE1	12.5 MHz to 25 MHz			spread	No	Yes	(FPT-8P-M07)	(ER type)									
MB88155PFT- G-113-JN-ERE1	25 MHz to 50 MHz				140	103											
MB88155PFT- G-400-JN-ERE1				Down	Yes	No	1										
MB88155PFT- G-402-JN-ERE1	12.5 MHz to	Multiplied	50 MHz to	spread	No	Yes											
MB88155PFT- G-410-JN-ERE1	20 MHz	by 4	80 MHz	80 MHz	80 MHz	80 MHz	80 MHz	80 MHz	80 MHz	80 MHz	80 MHz	Center	Yes	No			
MB88155PFT- G-412-JN-ERE1			spread		No	Yes	1										

■ PACKAGE DIMENSIONS





Please confirm the latest Package dimension by following URL. http://edevice.fujitsu.com/fj/DATASHEET/ef-ovpklv.html

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